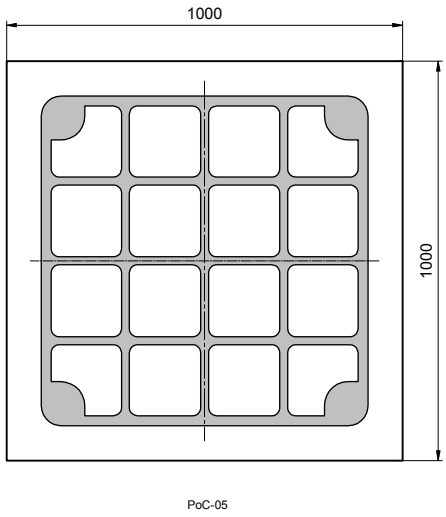
LED - Chip

ELC-590-11-05

discontinued 10.04.2007 rev. 02/06

Radiation	Type	Technology	Electrodes
Yellow	solderable	AlInGaP/GaAs	P (anode) up



typ. dimensions (µm)

typ. thickness
260 (±20) µm

cathode
gold alloy, 1.5 µm

anode
gold alloy, 1.5 µm

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F = 20 mA	V_F		1.8	2.0	V
Forward voltage	I_F = 100 mA	V_F		2.0		V
Reverse voltage	I_F = 10 µA	V_R	5			V
Radiant power[1]	I_F = 20 mA	Φ_e	0.45	0.6		mW
Radiant power[1]	I_F = 100 mA	Φ_e		2.8		mW
Luminous intensity[1]	I_F = 100 mA	I_V	400	550		mcd
Peak wavelength	I_F = 100 mA	λ_p	592	595	598	nm
Dominant wavelength	I_F = 100 mA	λ_D		592		nm
Spectral bandwidth at 50%	I_F = 100 mA	$\Delta\lambda_{0.5}$		17		nm
Switching time	I_F = 100 mA	t_r, t_f		25		ns

[1]Measured on bare chip on TO-18 header with *EPIGAP* equipment

Labeling

Type	Lot N°	Φ_e(typ) [mW]	V_F(typ) [V]	Quantity
ELC-590-11-05				

Packing: Chips on adhesive film with wire-bond side on top

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